IN THE SPECIFICATION:

At Page 1, after the title, please delete the sentence which referred to the parent application to the present divisional application, and replace that paragraph with the following rewritten paragraph.

-- This application is a divisional application of Application Serial No. 09/912,116, filed July 23, 2001, which ~~is currently pending~~ issued as U.S. Patent No. 6,703,169 on March 9, 2004. --

At Page 13, please replace Paragraph [0038] with the following rewritten paragraph.

-- [0038] Figure 4 is a graph 400 illustrating the stability of the critical dimension of a patterned line, in chrome, when a photomask substrate coated with photoresist, produced using the method of the present invention, is allowed to stand for time periods up to ~~365~~ 370 days prior to exposure to imaging radiation. - -

At Page 34, please replace Paragraph [0113] with the following rewritten paragraph.

-- [0113] Figure 4 shows a graph 400 of the critical dimension in nm obtained in chrome when a DX1100 DUV photoresist was applied over the same photomask substrate as that used in the Figure 3 specimens, with PAB at 105 °C for a time period of 9 minutes in ambient atmosphere prior to storage. After various periods of time, up to ~~365~~ 370 days of storage, imaging was carried out on test specimens using the direct write 257 nm ALTA ™ optical imaging tool described in detail above. After PEB at 88 °C for 7 minutes, the photoresist was developed, descummed, and the pattern in the photoresist was dry etch transferred to the underlying photomask substrate using the procedures described above. The mean CD in chrome for the photomask was measured. It was determined that the increase in mean CD was no more than 20 nm over the CD obtained when imaging was carried out immediately after photoresist coating of the photomask substrate. This

improvement is attributed to the combination of the type of photoresist (DX1100 DUV) and the PAB process. - -